MA3200W

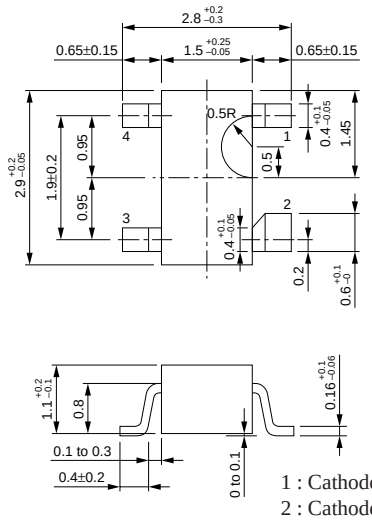
Silicon planer type

Constant voltage, constant current, waveform cripper and surge absorption circuit

■ Features

- Mini type package (4-pin)
- Two-element wiring in parallel of MA3200

Unit : mm



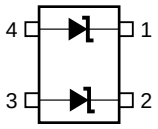
1 : Cathode 1
2 : Cathode 2
3 : Anode 2
4 : Anode 1
Mini Type Package (4-pin)

■ Absolute Maximum Ratings (Ta= 25˚C)

Parameter		Symbol	Rating	Unit
Average forward current	Single	$I_{F(AV)}$	100	mA
	Double	$I_{F(AV)}$	75	mA
Instanious forward current	Single	I_{FRM}	200	mA
	Double	I_{FRM}	150	mA
Total power dissipation	Single	P_{tot}*1	150	mW
	Double	P_{tot}*1	110	mW
Non-repetitive reverse surge power dissipation		P_{ZSM}*2	15	W
Junction temperature		T_j	125	˚C
Storage temperature		T_{stg}	– 55 to + 125	˚C

*1 With a printed-circuit board
*2 t=100µ s, T_j=125˚C

■ Internal Connection



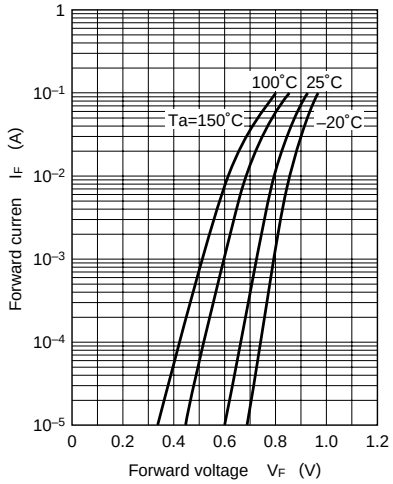
■ Electrical Characteristics (Ta= 25˚C)*1

Parameter	Symbol	Condition	min	typ	max	Unit
Forward voltage	V_F	I_F=10mA		0.8	0.9	V
Zener voltage	V_Z*2	I_Z= 5mA	17.0	20.0	22.0	V
Operating resistance	R_Z	I_Z= 5mA		15	55	Ω
Reverse current	I_R	V_R= 13V			50	µA
Temperature coefficient of zener voltage	S_Z*3	I_Z= 5mA	12.4	16.4	18.4	mV/˚C
Terminal capacitance	C_D	V_R= 0V, f=1MHz		36	60	pF

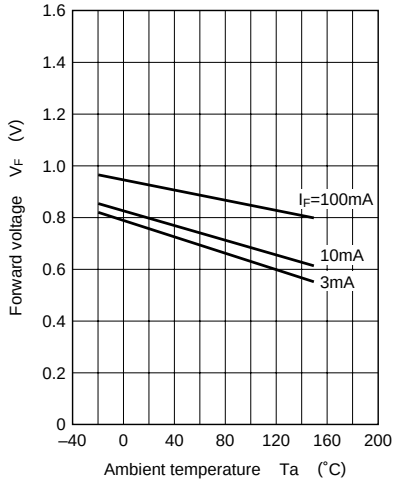
*1 : The V_Z value is for the temperature of 25˚C. In other cases, carry out the temperature compensation.
*2 : Guaranteeed at 20ms after power application
*3 : T_j= 25 to 125˚C

■ Marking

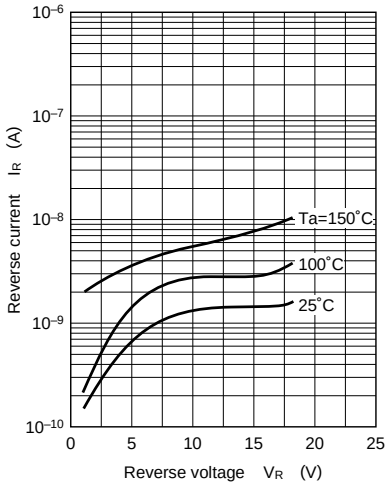
$I_F - V_F$



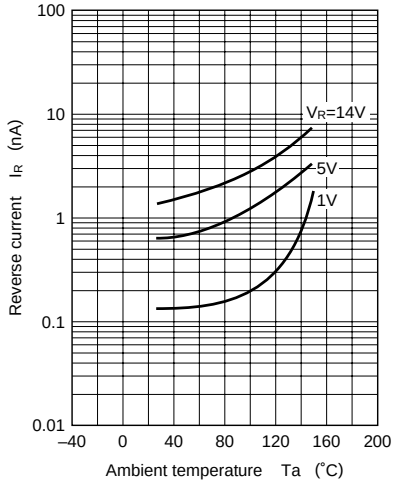
$V_F - Ta$



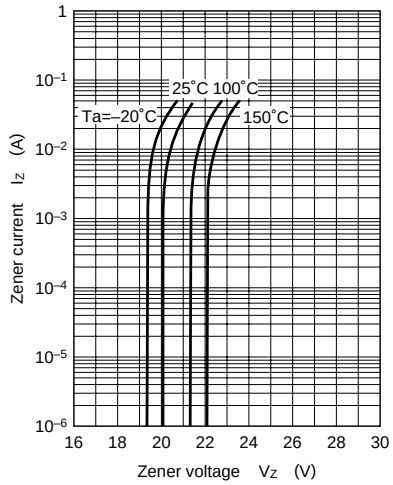
$I_R - V_R$



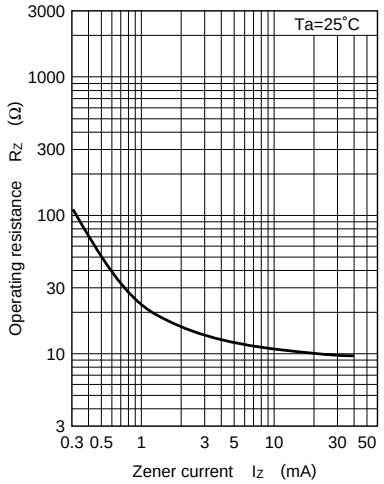
$I_R - Ta$



$I_Z - V_Z$



$R_Z - I_Z$



$C_t - V_R$